

## Claim Amendments

### Claim listing and status.

Claims 1 - 15 were filed with the application

No pending claims are amended.

New claims 16 and 17 are presented herewith

Claims 1 -4 are cancelled herewith.

Claims 5 - 15 are cancelled herewith.

### Claim instructions

Rewrite the content of claims 1 - 4 in amended form as new claim 16 as follows then cancel claims 1 - 4:

- 1     16. Protection in integrated circuitry from the effects of spike and surge over voltage
- 2     occurrences comprising:
- 3     an element deposited as an amorphous alloy, located in a field in the range of about
- 4     2Mv/cm and positioned between a node in said circuitry and a reference voltage,
- 5     said element having a body of a dielectric material taken from the group comprising
- 6     amorphous hydrogenated silicon carbide(SiCH), carbon doped oxides, SiCOH,
- 7     amorphous hydrogenated carbon(DLC), and fluorinated diamond like carbon(FDLC),
- 8     said element further having first and second essentially parallel faces separated by a
- 9     thickness dimension in the range of about 20 - 250 nanometers and
- 10    said element still further having conductive contact over each of said first and said second
- 11    faces.

Rewrite the content of claims 5 - 15 in amended form as new claim 17 as follows, then cancel claims 5 - 15.

1     17. The method of providing over voltage protection in an integrated circuit,  
2     comprising the steps of:  
3     positioning between a node in said integrated circuit and the reference voltage for said circuit  
4     a body of a dielectric material deposited in the form of an amorphous alloy,  
5     said dielectric material being taken from the group comprising amorphous hydrogenated  
6     silicon carbide(SiCH), carbon doped oxides, SiCOH, amorphous hydrogenated  
7     carbon, diamond like carbon(DLC), and fluorinated diamond like carbon(FDLC),  
8     said body of dielectric material having first and second essentially parallel surfaces  
9     separated by a thickness dimension with a conductive contact over each of said first  
10    and second surfaces,  
11    connecting said conductive contact on said first face of said body to said node in said  
12    circuitry, and,  
13    connecting said conductive contact on said second face of said body to said reference  
14    voltage for said circuitry.